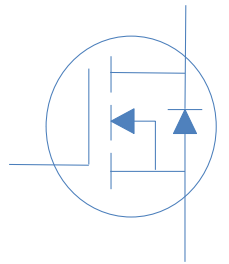
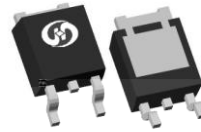


## 65V N-Ch Power MOSFET

H

$V_{DS}$		65	V
$R_{DS(on),typ}$	$V_{GS}=10V$	3.8	m
$R_{DS(on),typ}$	$V_{GS}=4.5V$	5.5	m
$I_D$ (Silicon Limited)		101	A

H



Part Number	Package	Marking
HGD046NE6AL	TO-252	GD046NE6AL

### Absolute Maximum Ratings at $T_J=25^{\circ}C$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^{\circ}C$	101	A
		$T_C=100^{\circ}C$	72	
Drain to Source Voltage	$V_{DS}$	-	65	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	340	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.1mH, T_C=25^{\circ}C$	31	mJ
Power Dissipation	$P_D$	$T_C=25^{\circ}C$	94	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	$^{\circ}C$

### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{JA}$	50	$^{\circ}C/W$
Thermal Resistance Junction-Case	$R_{JC}$	1.6	$^{\circ}C/W$



Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\text{ A}$			min
	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\text{ A}$	1.0		

- nA  
m

870

Total Gate Charge

Turn on Delay Time	$t_{d(on)}$		-	10	-	
Rise time	$t_r$	$V_{DD}=30V, I_D=20A, V_{GS}=10V,$	-	8	-	
Turn off Delay Time	$t_{d(off)}$	$R_G=10\ \Omega$	-	34	-	ns
Fall Time	$t_f$		-	10	-	

Reverse Diode Characteristics

Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_F=30A$	-	0.9	1.2	V
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Fig 1. Typical Output Characteristics

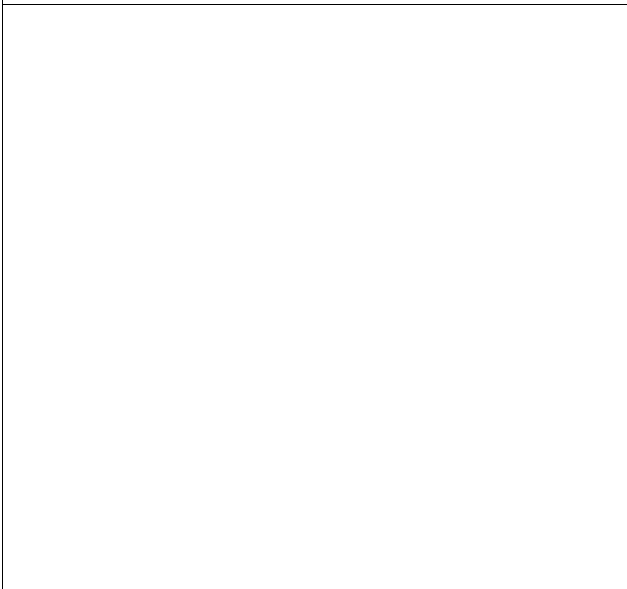


Figure 2. On-Resistance vs. Gate-Source Voltage

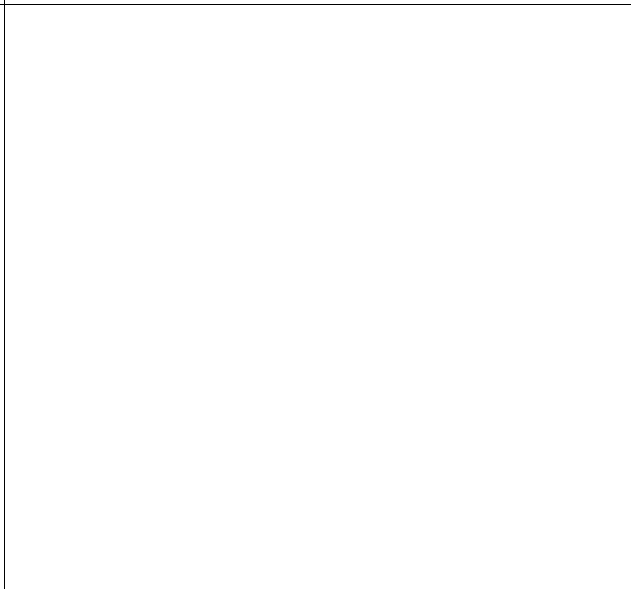


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

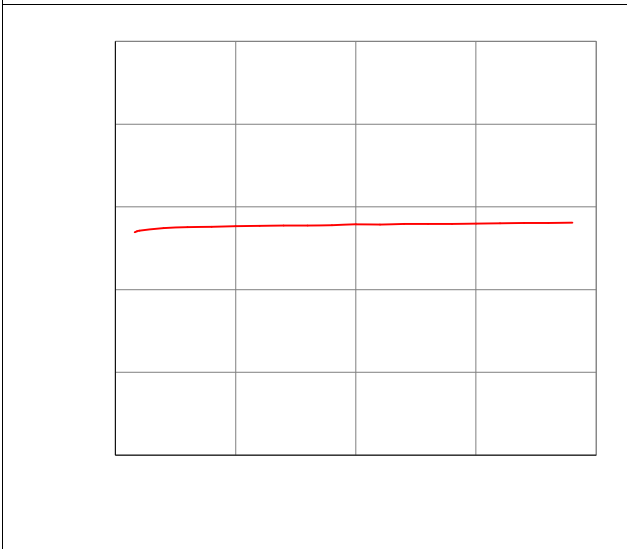


Figure 4. Normalized On-Resistance vs. Junction Temperature

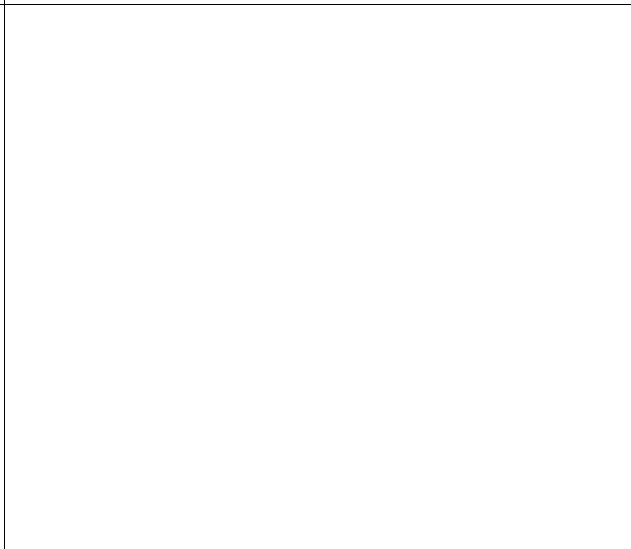


Figure 5. Typical Transfer Characteristics

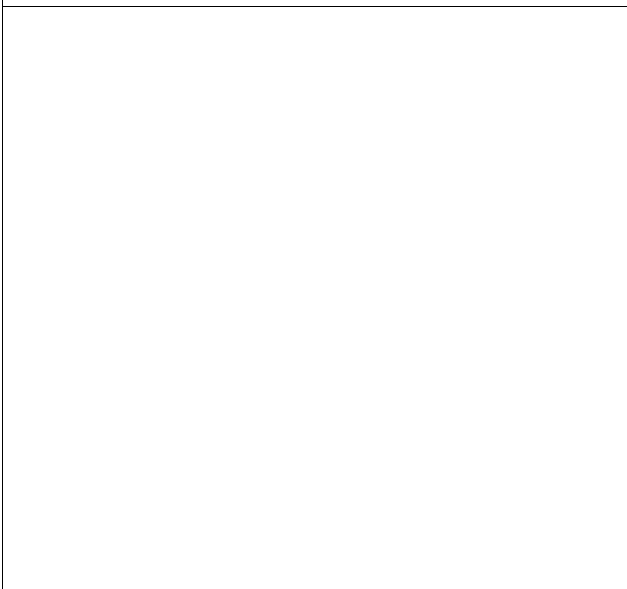


Figure 6. Typical Source-Drain Diode Forward Voltage

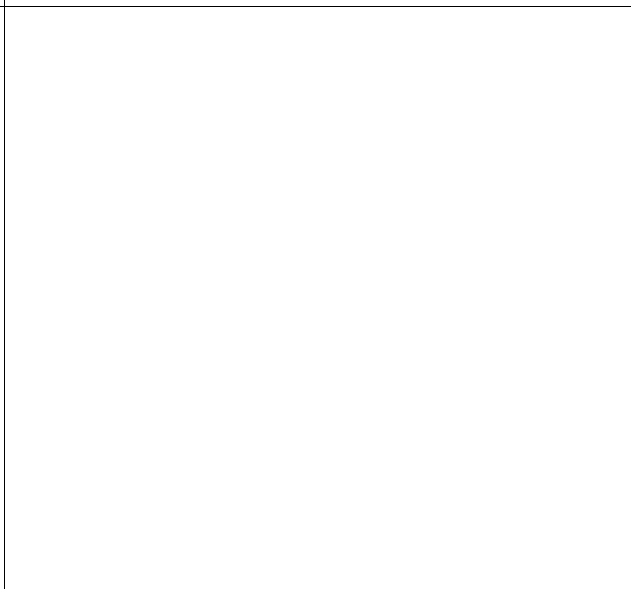


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

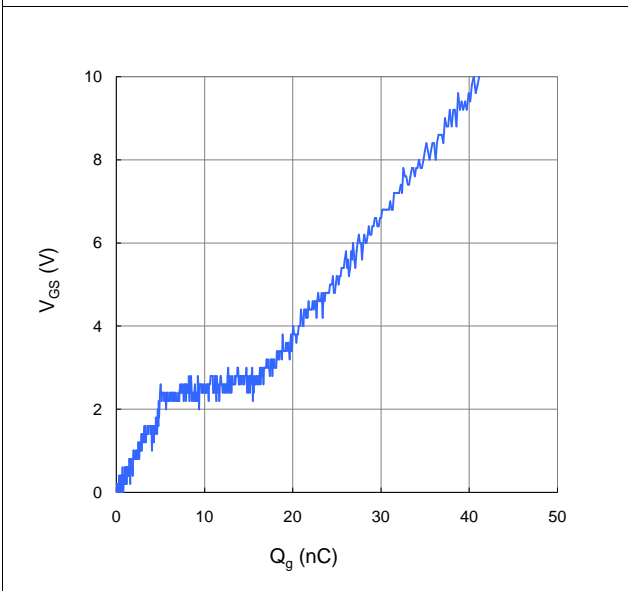


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

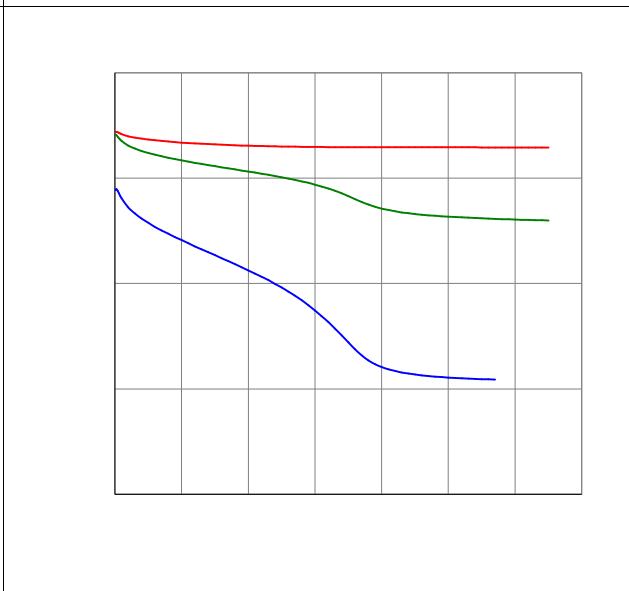


Figure 9. Maximum Safe Operating Area

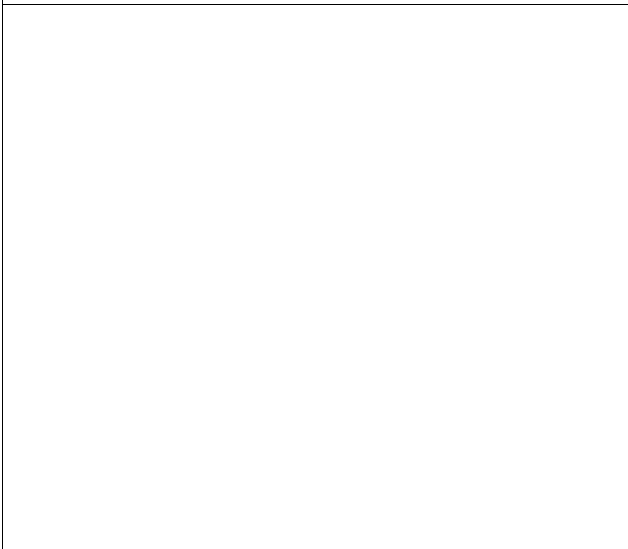


Figure 10. Maximun Drain Current vs. Case Temperature

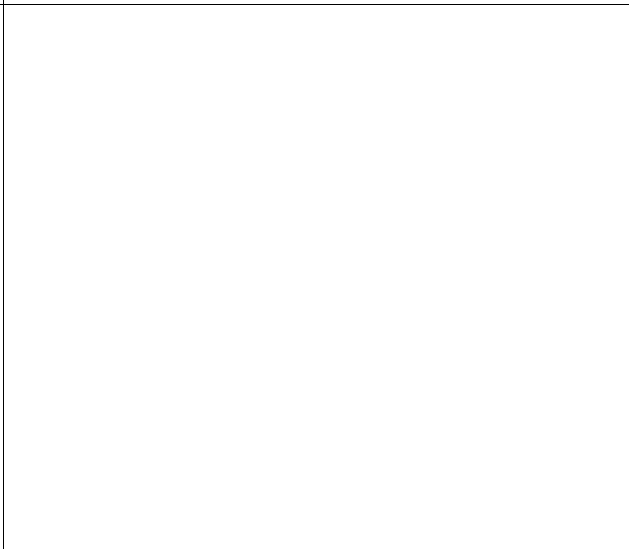
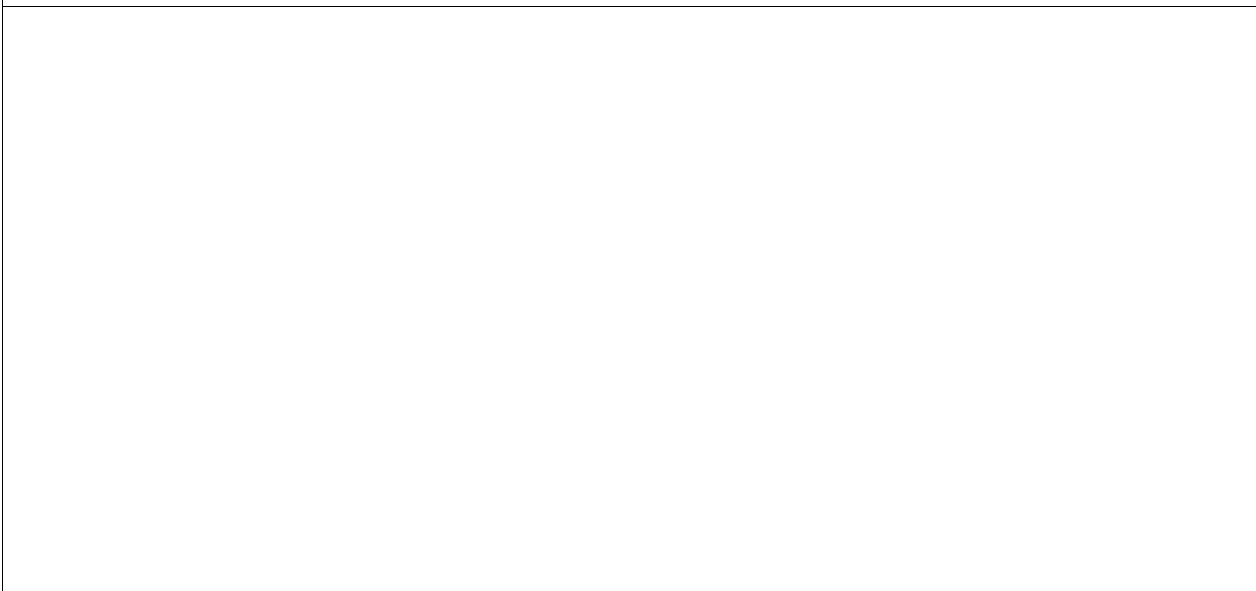
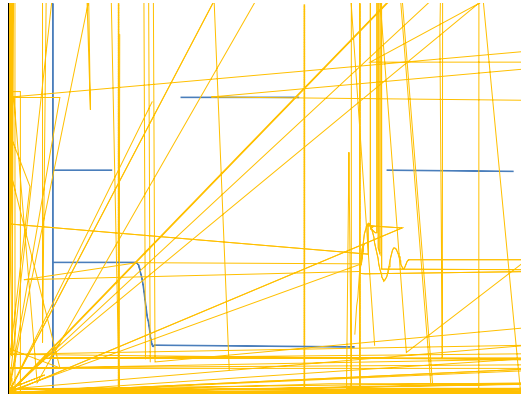
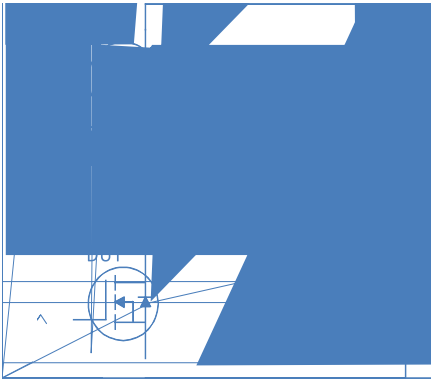


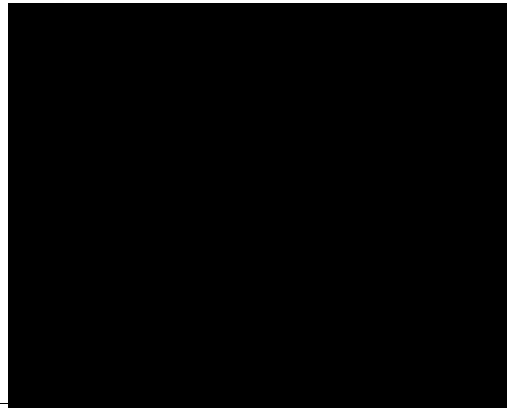
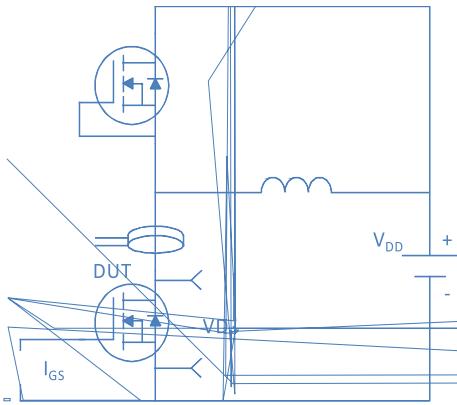
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



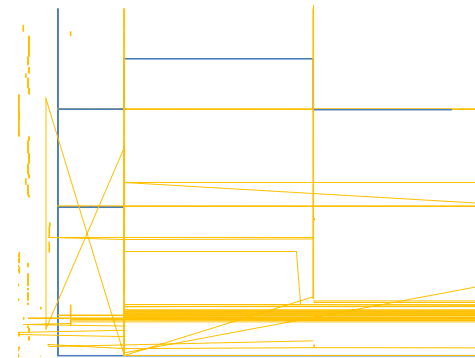
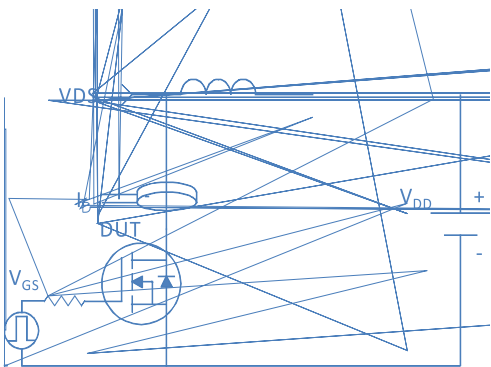
Inductive switching Test



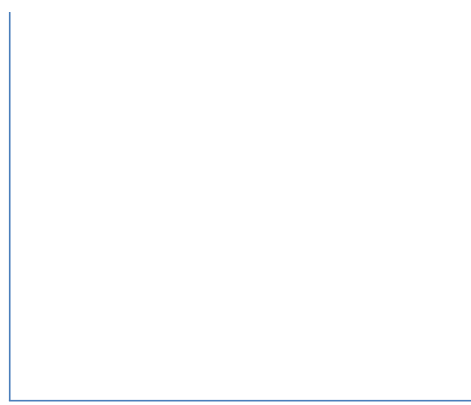
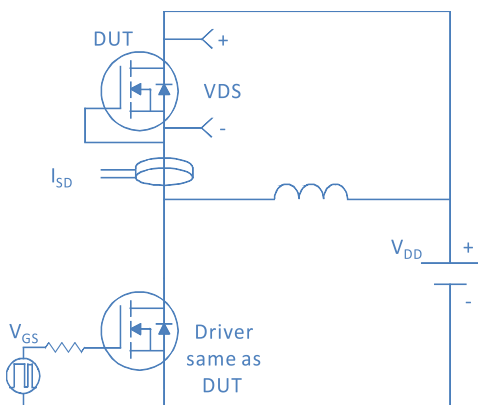
Gate Charge Test



Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



Package Outline